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L Number	Hits	Search Text	DB	Time stamp
-	1366860	semiconductor	USPAT;	2004/05/03 15:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	3311	hydrogen near2 anneal\$4	USPAT;	2004/05/03 15:07
-	3311	I nydrogen nearz annearpa	US-PGPUB;	2004/03/03 13.07
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/05/00 45:04
-	2	(hydrogen near2 anneal\$4) with sublim\$5	USPAT;	2004/05/03 15:21
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	52	(hydrogen near2 anneal\$4) and sublim\$5	USPAT;	2004/05/03 15:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	(hydrogen near2 ((heat adj treatment) or anneal\$4)) with	USPAT;	2004/05/03 16:00
		sublim\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	79	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:26
		sublim\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	4	(hydrogen near2 anneal\$4) same sublim\$5	USPAT;	2004/05/03 15:24
-	7	(hydrogen near 2 annear 47 same subminos	US-PGPUB;	2004/03/03 13.24
			EPO; JPO;	
			DERWENT;	
	2580	(b) (dragen near) ((best editrectment) or enneal(4)) and	IBM_TDB	2004/05/02 45:44
-	2560	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:41
		(insulat\$4 or (silicon adj dioxide))	US-PGPUB;	
			EPO; JPO;	
ł			DERWENT;	
	-	//	IBM_TDB	0004/05/55 45 45
-	71	((hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:47
		(insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj	US-PGPUB;	
		side) with substrate)	EPO; JPO;	
			DERWENT;	
		<u></u>	IBM_TDB	
-	16	((hydrogen near2 ((heat adj treatment) or anneal\$4)) and	USPAT;	2004/05/03 15:49
		(insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj	US-PGPUB;	
		side) with substrate) and ((((second or buttom) adj side) or	EPO; JPO;	
	İ	underside) with substrate)	DERWENT;	
			IBM_TDB	
-	6168	semiconductor and sublim\$5	USPAT;	2004/05/03 15:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12206	semiconductor and (insulat\$4 with (first or upper) with	USPAT;	2004/05/03 15:58
		(second or buttom) with side)	US-PGPUB;	
]		<u> </u>	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
L		<u></u>	100	

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-	7601	semiconductor and (substrate same (insulat\$4 with (first or	USPAT;	2004/05/03 15:59
		upper) with (second or buttom) with side))	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	91	(semiconductor and (substrate same (insulat\$4 with (first or	USPAT;	2004/05/03 16:01
	ŀ	upper) with (second or buttom) with side))) and (hydrogen	US-PGPUB;	
		near2 ((heat adj treatment) or anneal\$4))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	14	//	USPAT;	2004/05/03 16:03
		upper) with (second or buttom) with side))) and (hydrogen	US-PGPUB;	
		near2 ((heat adj treatment) or anneal\$4))) and (etch\$4 with	EPO; JPO;	
		insulat\$5 with (first or upper) with substrate)	DERWENT;	
	l		IBM_TDB	